P recision determ ination of band o sets in strained InG aA s/G aA s quantum wells by C-V-pro ling and Schrodinger-Poisson self-consistent simulation

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The results of measurements and numerical simulation of charge carrier distribution and energy states in strained quantum wells $\ln_x Ga_{1-x} A s/G aA s$ (0:06 6 x 6 0:29) by C-V-pro ling are presented. Precise values of conduction band o sets for these pseudom orphic QW shave been obtained by means of self-consistent solution of Schrödinger and Poisson equations and following tting to experimental data. For the conduction band o sets in strained $\ln_x Ga_{1-x} A s/G aA s - QW$ s the experimental data. For the conduction band o sets in strained $\ln_x Ga_{1-x} A s/G aA s - QW$ s the expersion $E_{-C}(x) = 0.814x$ $0.21x^2$ has been obtained.

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I. IN TRODUCTION

Since the developm ent of sem iconductor heterostructures the determ ination of energy band discontinuities of various sem iconductor pairs has been a very im portant task. Energy band o sets dom inantly control the electronic states in heterostructures and, hence, the output param eters of sem iconductor devices. The importance of getting true values of band o sets as well as the difculties in obtaining and, even more, in interpreting the relevant data have been attracting attention for the last 30 years. R. Dingle was one of the rst who reported in 1974-75^{1,2} the value of band o sets for isoperiodic heterosystem (Al-Ga)As/GaAs ("Dingle" rule 85:15). Then H.K roem $er_{r}^{3,4,5}$ G.Duggan⁶ and Yu et al.⁷ com prehensively reviewed the understanding of band o sets before 1991 and provided an overview of the m ethods com m only used in experimental band o set determination, mostly optical at that time. At the same time, the authors⁸ and others showed that a low sensitivity of the optical transition energies to the band o sets m ade its determ inations rather confusing. Up to now a great num ber of papers has been published on this subject (see bibliography in recent com prehensive review⁹). So far, how ever, as was pointed out in the review, am ong the ternary alloys used in quantum electronics, only the A IG aA s/G aA s system has generally accepted values of band o sets.

For one of the most important used heteropairs { $In_x G a_{1 x} A s/G aA s$ { as yet no clear picture about the dependence of band o sets on alloy composition has been obtained, despite the very intensive investigations in last years. The data collected by P.Bhattacharya¹⁰ show a great scatter of the values of relative conduction band o set E _c between 35% and 85% for x < 0.35. Above m entioned review⁹ reports relative conduction band o sets for the $In_x G a_{1 x} A s/G aA s$ { system in the range 57 90% and recommends as a rule of thum b E _c [eV] = x for x < 0.5. They conclude that no detailed study has yet been carried out on InG aA s-based heterojunctions. Recent publications on this subject^{11,12,13,14} only present partial results for di erent compositions, more or less agreed with "recommended" in Ref. 9. Theoretic calculations¹⁵ give the valence band o set for the end combination InA s/G aA s $E_V = 0.06 \text{ eV}$, which is in serious disagreement with experimental data.

One in portant device application of the heterosystem InG aA s/G aA s is high power laser diodes with strained quantum wells.¹⁶ In these structures thin quantum -size layers of InG aAs grow pseudom orphically, i.e. having the lattice constant of the underlying G aA s-layer in the plane of the hetero junction. The elastic energy, accumulated due to crystal cell distortion, causes the band structure of the thin InG aAs layer to be modied, 17 altering particularly its energy gap. Hence, in strained InG aA s/G aA s quantum wells one should expect another band o sets than in heterostructures with thick layers of the solid solution. In cases between pseudom orphic grow th and full strain relaxation (occurs in thick layers) the band o set in InG aA s/G aA s will have, obviously, som e interm ediate values. This fact explains, we suppose, the variety of data found in literature.

Numerical tting of C-V-curves^{18,19,20} by means of self-consistent solution of Schrodinger and Poisson equations is one of the most promising approaches to measure band o sets of quantum well structures.^{11,21,22} This approach correctly takes the quantization of carriers in a quantum well into consideration and yields very accurate results. However, well-de ned heterostructures are necessary for this.

C om plex multilayer structures like multiQ W s etc. and unknown dopant pro le or the presence of deep levels add sources of uncertainties. Therefore, in order to be sure to get precise values for band o sets at hetero junctions sim ple structures with a minimum of unknown parameters or parameters to be tted should be used.

This work presents accurate data for band o sets in heterostructures with strained pseudomorphic

 $In_xGa_{1 x}As/GaAs$ (0 < x < 0:3) quantum wells. To obtain these values we have carried out a system atic cycle of C-V-m easurem ents on specially fabricated structures. D etails of sam ple preparation and m easurem ents are described in Section II. In Section III the model for simulating measured concentration pro les and deriving the values of conduction band o sets based on self-consistent num erical solution of the Schrodinger and Poisson equations is described. The carrier concentration in the quantum well region is calculated on the base of a quantum -m echanical approach. M athem atical aspects of the computations are presented in Sections IIIA and IIIB. To increase the accuracy of the num erical calculations a non-uniform mesh with the mesh step inside the quantum well 10 times smaller than in the other regions has been used. Finally, in Section IV we present the results of num erical thing of experim entally measured C-V curves. The dependence of conduction band o set for strained pseudom orphically grown In_xGa_{1 x} As/GaAs -QW s has been obtained as a function of quantum well composition in the range 0.066×60.29 .

II. SAM PLE STRUCTURE AND M EASUREM ENT PROCEDURE

A special set of high quality sam ples with a sim pli ed structure (Fig. 1) containing In_xGa_{1 x} As/GaAs quantum wells of dierent width (w = 6:0 9:5 nm) and com position (x = 0.065 0.29) was grown on n⁺-GaAs substrates by MOVPE at deposition tem peratures of 650 C and 770 C. The GaAs cladding layers were uniform ly doped with Si, except for the QW sthem selves and thin (5 nm) spacer layers on both sides of the quantum well. To get the best experim ental results and to elim inate possible uncertainties in the subsequent num erical tting, the cap GaAs layer was designed to be 300 nm thick and have a constant doping level of (6 7) 10^{16} cm 3 . The width and composition of the QW s and cladding layers have been determined by high resolution X-ray di raction (HRXRD). AllQW swere fully strained without any relaxation seen in X-ray area maps.¹⁶ Ag-Schottky barriers were fabricated on top of the structures and 0 hm ic contacts were form ed on the substrate.

The parameters of the grown structures are listed in Table I.

The m easurem ents of capacitance-voltage characteristics and prolling of majority carriers in the quantum wells have been carried out with the help of a computer-controlled C-V-prollom eter at a testing frequency of 1 MHz and with an amplitude of the probing signal of 15 or 50 mV.

At zero bias the width of the space charge region under the Schottky-barrier in the sam ples was less than the thickness of the cap G aA s-layer. W ith increasing reverse bias the space charge region was broadened and its border crossed the quantum well. The C-V-characteristics of all sam ples clearly exhibit a plateau in the range of



FIG. 1: Layer sequence of the grown samples with $In_xGa_1 \times As/GaAs$ { quantum wells.



FIG.2: C-V-characteristics of $In_{0:225}Ga_{0:775}As/GaAsQW$ at di erent tem peratures (Sam ple # 307).

 $U_{rev} = 2$ 4.5 V related to discharging carriers in the QW .A typical example of $1=C^2 = f(U_{rev})$ characteristic for sample # 307 at di erent tem peratures is shown in Fig.2.

The apparent carrier distribution is derived from a measured C-V-curve using the well known formula for depletion approximation

$$n(d) = 2 \quad {}_{0}eA^{2}\frac{d}{dV} \quad \frac{1}{C^{2}} \quad i ; \qquad (1)$$

where is the dielectric constant (assumed to be equal for both the well and the barriers), e is the electron charge, A is the area of the Schottky diode. The depletion width

Sample	х	T deposition	d cap layer	QW width	E ofbound level	E _C
#		(C)	(m)	(nm)	at OV (m eV)	(m eV)
298	0.065	770	0.304	9.5	-10.9	57
299	0.14	770	0.304	0.8	-29.0	110
308	0.145	650	0.302	6.0	-25.0	110
303	0.145	650	0.305	7.5	-32.1	120
309	0.145	650	0.302	9.5	-35.1	120
296	0.19	770	0.295	6.5	-38.3	150
297	0.2	650	0.298	6.5	-39.5	155
306	0,215	770	0.304	7.2	-43.7	160
307	0.225	770	0.308	7.4	-48.8	175
300	0.23	770	0.304	7.2	-48.5	175
301	0.27	770	0.300	6.5	-54.6	210
305	0.29	650	0.300	6.0	-55.3	220

TABLE I: Characteristics of the structures and results of numerical simulation of conduction band discontinuities in $In_x Ga_{1-x} A s/GaA s$ strained quantum wells grown by MOVPE.

d is given as usual by

$$d = \frac{{}_{0}A}{C} :$$
 (2)

Figure 3 shows some examples of the n d curves covering the whole range of QW compositions. The proles exhibited a clear dependence of am plitude, width, and the depth of depletion on the composition and the width of the QW s. It is worth to note that beyond the regions of accum ulation and depletion related to the QW the carrier concentration was excellently constant, and we used it in the tting of the experimental pro les to the simulated ones on the base of self-consistent solution of the Schrodinger and Poisson equations by varying the band o set.

III. MODEL FOR SMULATING C-V PROFILES

For simulating the $\ensuremath{\mathsf{C}}\xspace$ -V -characteristics the Poisson equation

$$\frac{d}{dz} = {}_{0} (z) \frac{d'(z)}{dz} = e N_{D}^{+}(z) n(z)$$
(3)

has been solved, where ' (z) is the electrostatic potential, n (z) is the free carrier concentration, and N $_D^+$ is the concentration of ionized donors. The boundary conditions for (3) at the Schottky barrier and in the electroneutrality region, far away from the QW, are:

$$(0) = U + '_{bi};$$
 (4)

$$'(1) = 0;$$
 (5)

Here U is the applied voltage, and $'_{\rm bi}$ is the built-in potential.

In addition, the m atching conditions for the potential at both heterointerfaces have to be fullled

$$barr \frac{d'_{barr}}{dz} = well \frac{d'_{well}}{dz}:$$
 (6)

The indexes "barr" and "well" correspond to the regions of G aA s barrier and InG aA s quantum well, respectively.

The free carrier concentration n(z) in (3) far from the QW can be calculated as in the case of a hom ogeneous structure through the Ferm i integral

n (z) = N_C
$$\frac{2}{p-F_{1=2}}$$
 $\frac{E_C E_F e'(z)}{kT}$; (7)

where N_C is the elective density of states in the conduction band, E_F is the Ferm i level, T is the temperature, and k is the Boltzmann constant. In contrast, in the vicinity of a quantum well the carrier concentration should be calculated by solving Schrodinger's equation. The needed spatial distribution of the electrostatic potential was derived using a procedure of self-consistency of the Schrodinger and Poisson equations. The essence of the procedure is the sequential (step-by-step) solution of Schrodinger and Poisson equations until convergence.^{21,23,24} A s a criterion of convergence we took an increment of the potential of less than 10⁸ V in the next iteration.

Quantum size e ects are important only inside the quantum well and in its immediate vicinity. So for numerical solution of the Schrodinger equation we used a "quantum box", a narrow region containing the QW (Fig. 4). The optimal width of the quantum box was chosen experimentally during simulations, in order to achieve a high precision in determination of the quantized carrier concentration, and, in balance, to reduce the computing time. The quantum box width was chosen as nine times the width W of the corresponding quantum



FIG.3: C-V-pro ling of $\ln_x G a_{1-x} A s/G aA s$ quantum wells. Samples # 296{# 309. a) Common view of apparent carrier concentrations for several samples, T = 300K; b) Apparent concentration peak values as a function of x.

Note that near x = 0.14 there are 4 samples with di erent width of Q W .

well, which was placed in the center of the quantum box.

A coording to the boundary conditions, there must be nodes of the wave functions at the edges of the quantum box. For this reason the data calculated close to the quantum box boundaries are dropped. The length of this region is no more than 1 W, as can be seen from Fig. 4. On the other hand, at distances about 2 3 W from the QW the quantization e ect is very weak, and there we can use the Ferm i integral (7) for deriving the free carrier concentration. The coincidence of the concentration pro les at this part derived from quantum - m echanical approach and from (7) was used as the proof for a true solution.



FIG.4: Scheme of computations. The "quantum box" is shaded.1 | Schrödinger's concentration; 2 | concentration derived from (7); 3 | resulting calculated "apparent" concentration (m atched the experim ent).

A. Solving the Poisson equation

The Poisson equation has been solved numerically by Newton's method relative to the correction term .

The great di erence (tenfold) in the values of electron and hole e ective m asses in G aAs and nearby ternary InG aAs alloys m akes the Ferm i level shift toward the bottom of the conduction band. Therefore, a signi cant part of donors (up to 30%) remains non-ionized at room tem perature, even despite the very low ionization energy of Sidonors in G aAs (about 5 m eV²⁵). Because of this, the incom plete donor ionization has to be taken into account.

To reduce the computation time, it is desirable to use some approximation of the Ferm i integral (7). The sim – plest exponential approximation is not applicable here because of the close position of the Ferm i level to the bottom of the conduction band. There is another well known approximation for (7) by the expression

n (z) =
$$\frac{N_{C}}{C_{n} + \exp \frac{E_{C} - E_{F} - e'(z)}{k_{T}}}$$
; (8)

that betterm atches the Ferm i integral. The constant C $_{\rm n}$ here usually falls between 0.17 and 0.35. 26

In order to m inim ize the approximation error and to full the electroneutrality condition on the right-hand side of the simulated region (i.e. in the G aA s substrate) we used the following procedure: by solving the electroneutrality equation and using expression (7) the Ferm i level position is determined at $\prime = 0$. Then equating (7) to (8) one can derive the current adaptivity constant C_n. At another ' the maximum relative error of such approximation does not exceed 3 $\,$ 10 4 .

The electrostatic potential was written as an initial approximation $\prime_0(z)$ and a correction term $\prime(z)$:

$$'(z) = '_{0}(z) + '(z)$$
: (9)

To linearize the Poisson equation (3) the expression for n was decomposed into a Taylor series including linear term relative to the correction \prime (z).

Then a nite-di erence analog of the Poisson equation has been rewritten as a system of linear equations with a characteristic three-diagonal form. To get a high precision solution in a reasonable time di erent mesh steps were used inside and outside the quantum box. The num ber of points in the mesh was 8000, including about 1500 in the quantum box. The G auss method was applied to solve the system with som e modi cations based on obvious symmetry of the equations.

A fier getting the correction \prime (z) a new potentialwas obtained according to (9).

B. Solving the Schrodinger equation

The e ective mass, one-dimensionalSchrodinger equation can be written as 24

$$\frac{-2}{2} \frac{d}{dz} \frac{1}{m(z)} \frac{d_{i}(z)}{dz} + V(z)_{i}(z) = E_{i}(z); \quad (10)$$

where E_i are the eigenvalues, i are the corresponding eigenvectors, m is the coordinate-dependent electron effective m ass. V (z) is the electric potential energy:

$$V(z) = \begin{pmatrix} e'(z) + E_{C} & \{ \text{ inside } QW, \\ e'(z) & \{ \text{ outside } QW. \end{pmatrix}$$
(11)

E $_{\rm C}$ is the conduction band o set.

W e used boundary conditions of Neum an's type at the ends of the quantum box.

The nite-di erence analog for (10) was obtained using the three point form ula

$$\frac{2}{2m_{j}} \frac{i_{j} + i_{j} + i_{j} + 1}{h_{j}^{2}} + V_{j} + V_{j} = E_{i} + i_{j}; \quad (12)$$

where j identi es the point on the one-dimensional mesh, and h_j is the distance between the mesh nodes (a step of the mesh).

In addition to boundary conditions, at the hetero junctions the following matching conditions should be maintained between the derivative of wave functions inside and outside the quantum well:

$$\frac{1}{m_{\text{barr}}} \frac{h_{\text{barr}}}{h_{\text{barr}}} = \frac{1}{m_{\text{well}}} \frac{h_{\text{well}}}{h_{\text{well}}}$$
(13)

The Schrodinger equation (10) was solved num erically by the well known "shooting" method with some im provem ents aim ed to reduce the computation tim e. The number of points in the mesh should be enough to eliminate the error due to substitution of the derivative with the nite-di erence approximation (12). We compared the results of numerical solution of (10) by the shooting method with the well known analytical solution for a rectangular quantum well.²⁷ It was found that the mesh size of about 1500 points yields quite good accuracy with a relative error in eigenvalue determination less than 10³ for alm ost all levels.

A fler the set of eigenvalues E_i and corresponding eigenvectors $_i(z)$ had been obtained, the carrier concentration in the region of QW was calculated via local density of states from the expression^{21,22}

$$n(z) = \frac{m(z)kT}{\sim^2} \sum_{i}^{X} ln 1 + exp \frac{E_F E_i}{kT} j_i(z) j_i^2;$$
(14)

using the condition of norm alizing the wave functions

$$\int_{1}^{+1} j_{i}(z) \int_{2}^{2} dz = 1:$$
 (15)

Sum m ation in (14) runs over all subbands.

Ζ

The prefactor in the expression (14) before the square of wave function is considered as the number of electrons per unit area in the ith - subband.

In the quantum well region the concentrations of both bound and free electrons were calculated from the Schrodinger equation. We consider this a more correct approach than the simple summation of bound (inside QW) and free carriers (above QW) used, for example, in Ref. 22. But, due to the nite width of the quantum box the continuum of free electron states in this scheme e of computations is represented by a set of discrete levels with energies determined by the size of the quantum box.

In order to sum up all charge carriers in the quantum well region we took into account the 16 lowest energy levels. Fig. 5 shows the occupation of the 16 energy levels at di erent bias. The carrier concentration in the rst subband n_1 was at least ten times greater than in the second one, and the concentration in 16th subband (and all higher subbands) is below 10⁻⁷ of n_1 and can be neglected.

The results of the computation of energy states in dependence of applied reverse bias for the sample # 300 (E $_{\rm C}$ = 175 m eV) are shown in Fig. 6(a), and a lineup of the conduction band bottom for this structure is depicted in Fig. 6(b). As can be seen, a single bound level is observed in the structure with an energy of 49 m eV in equilibrium. (The bottom of the conduction band in the electroneutrality region was taken as zero). Starting approximately at 2:5 V the space charge regions of the Schottky barrier and the QW merge (Fig. 7), and the penetrating electric eld bends the conduction band bottom near the QW, forcing the bound level to lift up. At U = 5 V the level becomes unbound.

To calculate the C-V characteristics so called "quasistatic approach"²⁸ was applied. The capacitance of a



FIG. 5: Electron concentration in rst 16 energy subbbands (relative units) at di erent reverse biases. Sam ple # 300 (E $_{\rm C}$ = 175 m eV), T = 300K.

structure is the rst derivative of the total charge. The latter can be derived via the ow of electric eld across the surface according to the G auss theorem . The spatial distribution of electrostatic potential' is calculated during solution of the Poisson equation, so one can derive the value of the electric eld at the surface at di erent applied biases:

$$E_{surf} = \frac{\prime_{1} \prime_{0}}{h_{bulk}}; \qquad (16)$$

and, hence, build up the capacitance-voltage characteristic (or restore the apparent concentration pro le) using (1).

IV. RESULTS OF SIM ULATION AND DISCUSSION

A s has been established earlier,^{20,29} there exists a certain discrepancy between the true and "apparent" concentration pro les of free charge carriers near a heterojunction, a quantum well or a quantum dot.^{30,31,32} An apparent pro le, obtained in experiment, is more smeared in comparison to the true one and has a shift in the peak position (see Fig. 4). The general reason for this discrepancy is the indirect and non-equilibrium procedure of concentration pro le restoration from C -V m easurements. Generally, this technique involves di erentiation of the C -V -curve (1) in the approximation of fully depleted space charge region and does not take into account the problem of D ebye smearing. In the case of Q W pro ling, where one expects sub-D ebye resolution, this standard technique leads to an essential distortion



FIG.6: Results of num erical calculations for sample # 300 (x = 0.23; well width = 7.2 nm; o set E _c = 175 meV): a) rst 8 energy levels as a function of U_{reV}; b) the bottom of conduction band near the QW at di erent U_{reV}.

of the apparent pro le. So, for the goal of adequate tting, during simulations we must accomplish just the same procedure of restoring the apparent pro leas in real experiment and, particularly, the bias voltage increment in the simulation must be equal to the voltage step used in the experiment.

The results of tting for two sam ples are presented in F igs. 8 and 9. As can be seen, excellent m atching is obtained. This proves the correctness of the used m odel. O ne should underline again that due to the high quality of the specially fabricated for C -V-m easurem ents sam ples no additional adjustable parameters like an impurity concentration gradient or a charge at the hetero junction had to be used in the tting procedure. The only tting parameters was the conduction band o set, E _ C. The value



FIG.7: Simulated concentration proles of electrons in the region of QW at U = 1 V (solid) and 2:5 V (dashed line). Sample # 300.

of m a jority carrier concentration was taken on the shoulders of the m easured concentration proles. Parameters for $\ln_x G a_{1-x} A s$, needed for the calculations, were taken from 25,33 Fig. 9 also demonstrates the resolution of our tting. For a medium In-content (x = 0.14) the error was less than 10 m eV. It was found that the resolution is approximately directly proportional to the alloy com position of the quantum well. In general, we estimate the relative error in the determ ination of band o sets as less than 10% within the measured range of x.

An interesting example of thing for the sample with the smallest In-content in QW (x = 0.065, sample # 298) is presented in Fig. 10. Here the apparent peak of enrichment in the QW is even smaller than the value of the impurity concentration, despite the spatial connement inside the QW. The simulated prole in this case is very sensitive to the band o set (the error is about 5 m eV), how ever, the thing is not as good as for other compositions. For such a weak concentration peak the presence of residual impurities in the quantum well and in adjacent spacers begins to play an essential role. One also should bear in m ind for explanation the increased relative value of the experimental noise.

In Table I we sum marized the conduction band o sets in strained pseudom orphically grown $In_x G a_{1 x} A s/G aA s$ (0.06 6 x 6 0.29) quantum wells obtained in our study. Only one bound level was observed in all samples. Its depth in equilibrium (U = 0 V) is depicted in Fig.11 as a function of composition. One can see that for compositions x < 0.25 the level appears above the corresponding Ferm i level. Nevertheless, the occupation in the subband remains signi cant to provide an excess of apparent carrier concentration in QW region over the dopant value in



FIG. 8: Experimental (dots) and tted (solid) apparent concentration proles of $In_{0:23}Ga_{0:77}As/GaAs$ quantum well. (Sam ple # 300, T = 300K).Best t E $_{\rm C}$ = 175 meV.



FIG.9: Resolution of the tting. The results for the best t ($E_c = 120 \text{ meV}$, solid line) and for $E_c = 130 \text{ meV}$ (dashed line) are presented. Dotted curve | the experimental apparent pro le for sample # 303 (x = 0:145).



FIG. 10: Apparent concentration prole of $\ln_x Ga_1 \times As/GaAs$ quantum well with low In-content $x_{In} = 0.065$ (dotted) and tted curve (solid) with E $_c = 55$ m eV. (Sam ple # 298, T = 300K).

all samples, except for x = 0.065.

From Fig. 11 it can be seen that there is no bound energy level for x < 4%. Indeed, the weak doping in the adjacent to QW spacers leads to an additional conduction band bending near the QW, which lifts the energy level up. The e ect of disappearing bound level does not exist if the spacers are absent (at least, down to extrem ely low x, about 1%, when errors in num erical calculations begin to occur).

In Fig. 12 the results on conduction band o sets in strained In_xGa_{1 x} As/GaAs-QW s obtained during the num erical tting to the experim ental C-V characteristics are presented. The "recommended" curve from the above mentioned review⁹ is also depicted. The "recom mended" values of band o sets are higher by about 25% in comparison to our results for strained quantum wells. The origin of this di erence most probably is the presence of signi cant degree of elastic strain in pseudom orphic InG aA s on G aA s. The deform ation potential in com pressively strained InG aAs modi es the energy lineups of the heterostructure. Estimations on the base of m odel-solid theory³⁴ predict an increase of the band gap of compressively strained InG aAs in comparison to the value E_q for bulk material (this e ect again is of the order of 25%). So, the absolute values of band discontinuities are smaller in compressively strained quantum wells than in relaxed single heterostructures or thick double heterostructures. Recent results of other researchers on strained QW s, mainly obtained by capacitance techniques (also depicted in Fig. 12), are in reasonable agree-



FIG. 11: Position of bound energy level E_1 in strained $\ln_x Ga_{1 \ x} As/GaAs QW s$ (triangles up for w 7.2 nm and triangles down for w > 7.2 nm). Solid line | calculated dependence E_1 of x_{In} in the assumption w = 7.2 nm and for the doping concentration as in the sample # 300. Dash-dot line | the corresponding position of Ferm i level.



FIG. 12: Conduction band o sets in strained $In_xGa_1 \times As/GaAs QWs$ as a function of composition. D ashed line | as recommended in Ref. 9. Open circles | the latest results of capacitance and optical investigations on strained $In_xGa_1 \times As/GaAs \{QW s: 1 \ Ref. 14; 2 \ Ref. 18; 3 \ Ref. 13; 4 \ Ref. 11.$

m ent with ours, but exhibit signi cant scattering.

The experimentally obtained dependence $E_c = f(x)$ is close to a straight line with only little bowing. From tting the curve to a parabola we propose the expression $E_c(x) = 0.314x \quad 0.21x^2$ for the conduction band o - sets in strained $In_x Ga_{1-x} A s/G aA s$ quantum wells in the

V. SUMMARY

A in ing to get accurate and precise values for conduction band o sets, a set of high quality sam ples containing strained $In_x Ga_{1-x} A s/G aA s quantum wells was grown in$ the composition range 0.06 6 x 6 0.29. Specially forC-V-m easurements a constant in purity concentration inthe cladding layers was maintained during the growthin order to eliminate uncertainties in subsequent num erical simulations. A tting procedure of experimentally

- ¹ R.Dingle, W.Wiegmann, and C.H.Henry, Phys.Rev. Lett. 33, 827 (1974).
- ² R.Dingle, A.C.Gossard, and W.Wiegmann, Phys.Rev. Lett. 34, 1327 (1975).
- ³ H.K roem er, Surf. Sci. 132, 543 (1983).
- ⁴ H.Kroemer, J.Vac.Sci.Technol.B 2,433 (1984).
- ⁵ H.Kroemer, Surf. Sci. 174, 299 (1986).
- ⁶ G.Duggan, J.Vac.Sci.Technol.B 3, 1224 (1985).
- ⁷ E.T.Yu, J.O.M cCaldin, and T.C.M cG ill, Solid State Phys. 46, 1 (1992).
- ⁸ B.Jogaiand P.W .Yu, Phys. Rev. B 41, 12650 (1990).
- ⁹ I. Vurgaffm an, J. R. Meyer, and L. R. Ram Mohan, J. Appl. Phys. 89, 5815 (2001).
- ¹⁰ P. Bhattacharya, ed., Properties of lattice m atched and strained Indium Gallium Arsenide (IN SPEC, London, 1993).
- ¹¹ J. Arias, I. Esquivias, E. C. Larkins, S. Burkner, S.W eisser, and J.Rosenzweig, Appl. Phys. Lett. 77, 776 (2000).
- ¹² P. Disseix, J. Leymarie, A. Vasson, A.M. Vasson, C.Monier, N.G randjean, M. Leroux, and J.M assies, Phys. Rev. B. 55, 2406 (1997).
- ¹³ G.Karunasiri, J.Appl.Phys.79, 8121 (1996).
- ¹⁴ L.Lu, J.W ang, Y.W ang, W.Ge, G.Yang, and Z.W ang, J.Appl Phys. 83, 2093 (1998).
- ¹⁵ S.H. W ei and A. Zunger, Appl. Phys. Lett. 72, 2011 (1998).
- ¹⁶ F.Bugge, U.Zeimer, M.Sato, M.Weyers, and G.Trankle, J.Cryst.Growth 183, 511 (1998).
- ¹⁷ J.H.D avies, The physics of low-dimensional sem iconductors: an introduction (C am bridge University Press, 1998).
- ¹⁸ X. Letartre, D. Stievenard, and E. Barber, Appl. Phys. Lett. 58, 1047 (1991).
- ¹⁹ S. Subram anian, B. M. Arora, A. K. Srivastava, G. Fernandes, and S. Banerjee, J. Appl. Phys. 74, 7618 (1993).

obtained apparent concentration proles has been in plem ented using self-consistent solution of Schrodinger and P oisson equations. All important information about the properties of the quantum well structures was derived: the majority carrier proles, the positions of energy levels, corresponding wave functions, prole of the conduction band bottom, as well as the dependencies of the above mentioned parameters on the applied electric eld. The presence of only one bound level was discovered in all samples. The conduction band o sets in strained $\ln_x G a_1 \ge A s/G aA s quantum wells follow the expression$ $E_C(x) = 0.814x = 0.21x^2$.

- ²⁰ B.M. Tschimer, F.M orier-Genoud, D.M artin, and F.K. Reinhart, J.Appl. Phys. 79, 7005 (1996).
- ²¹ I.H. Tan, G.L. Snider, L.D. Chang, and E.L. Hu, J. Appl. Phys. 68, 4071 (1990).
- ²² P.N.Brounkov, T.Benyattou, and G.Guilbt, J.Appl. Phys. 80, 864 (1996).
- ²³ F.Stem, Phys. Rev. B.5, 4892 (1972).
- ²⁴ F.Stem and S.D.Sam a, Phys. Rev. 30, 840 (1984).
- ²⁵ S. Adachi, Physics Properties of III-V Sem iconductors Compounds (John W iley & Sons, New York, 1992).
- ²⁶ A.Abou-Elnour and K.Schuenem ann, J.Appl.Phys.74, 3273 (1993).
- ²⁷ L.D. Landau and E.M. Lifshitz, Quantum Mechanics (Pergamon, New York, 1977), 3rd ed.
- ²⁸ W .C. Johnson and P.T. Panousis, EEE Trans. Electron D evices ED -18, 965 (1971).
- ²⁹ H.Kroemer, W.-Y.Chien, J.J.S.Harris, and D.D.Edwall, Appl. Phys. Lett. 36, 295 (1980).
- ³⁰ P. N. Brunkov, A. A. Suvorova, M. V. Maximov, A. F. Tsatsul'nikov, A. E. Zhukov, A. Y. Egorov, A. R. Kovsh, S.G. Konnikov, T. Inn, S.T. Stoddart, et al., in Int. Symp. Nanostructures: Physics and technology (StPetersburg, 1997), p. 236.
- ³¹ C.M.A.Kapteyn, F.Heinrichsdor, O.Stier, R.Heitz, M. Grundmann, N. D. Zakharov, D. Bimberg, and P.Werner, Phys. Rev. B 60, 14265 (1999).
- ³² V.I.Zubkov and A.V.Solom onov, in Int. Symp. Nanostructures: Physics and Technology (StPetersburg, 2001), pp.244{247.
- ³³ M. Levinshtein, S. Rum yantsev, and M. Shur, eds., Temary and quaternary III-V compounds, vol. 2 of H andbook series on sem iconductor parameters (W orld Scientic, London, 1999).
- ³⁴ C.G.Van de W alle, Phys.Rev.B 39, 1871 (1989).